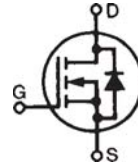


Depletion Mode MOSFET

IXTA1N170DHV
IXTH1N170DHV

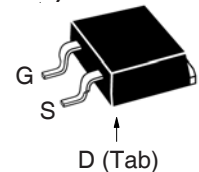
$$\begin{aligned} V_{DSX} &= 1700V \\ I_{D(on)} &\geq 1A \\ R_{DS(on)} &\leq 16\Omega \end{aligned}$$

N-Channel

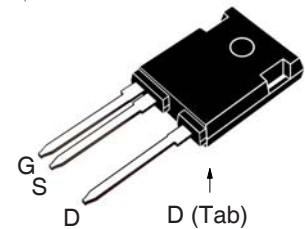


Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700	V
V_{DGX}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	1700	V
V_{GSX}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
P_D	$T_C = 25^\circ\text{C}$	290	W
T_J		- 55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		- 55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
F_C	Mounting Force (TO-263HV)	10..65 / 22..14.6	N/lb
M_d	Mounting Torque (TO-247HV)	1.13/10	Nm/lb.in
Weight	TO-263HV	2.5	g
	TO-247HV	6.0	g

TO-263HV (IXTA)



TO-247HV (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Features

- Normally ON Mode
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-Up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSX}	$V_{GS} = -5V, I_D = 250\mu A$	1700		V
$V_{GS(off)}$	$V_{DS} = 25V, I_D = 250\mu A$	- 2.5		- 4.5 V
I_{GSX}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100 nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}, V_{GS} = -5V$ $T_J = 125^\circ\text{C}$			10 μA 100 μA
$R_{DS(on)}$	$V_{GS} = 0V, I_D = 0.5A$, Note 1			16 Ω
$I_{D(on)}$	$V_{GS} = 0V, V_{DS} = 50V$, Note 1	1.0		A

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

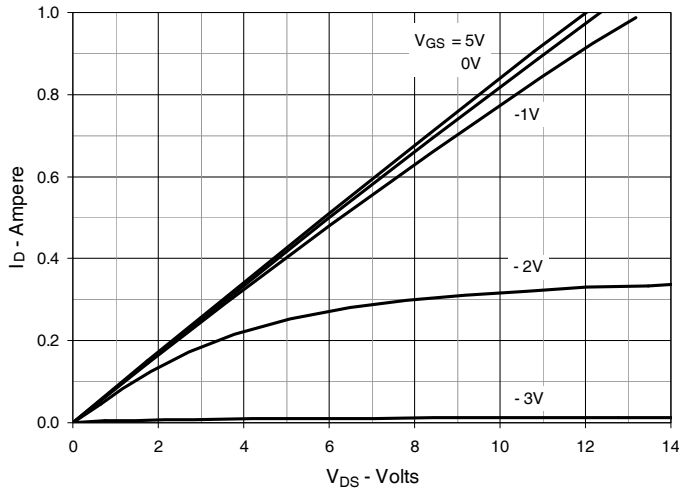


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

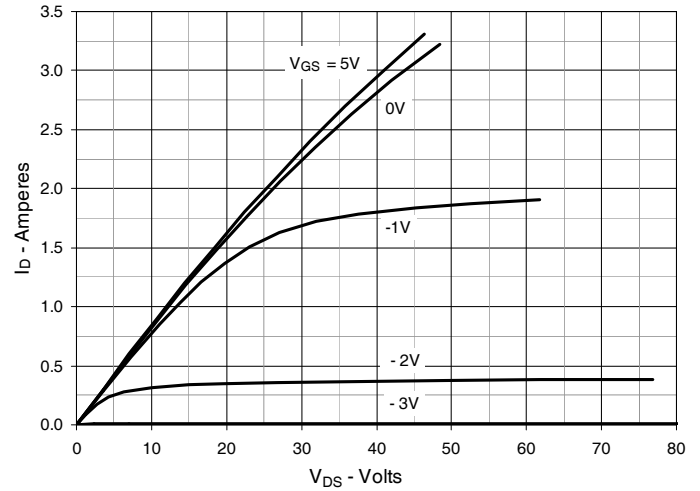


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

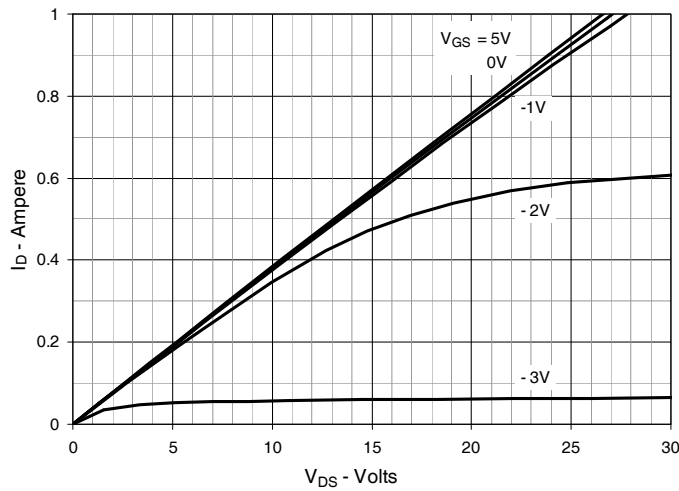


Fig. 4. Drain Current @ $T_J = 25^\circ\text{C}$

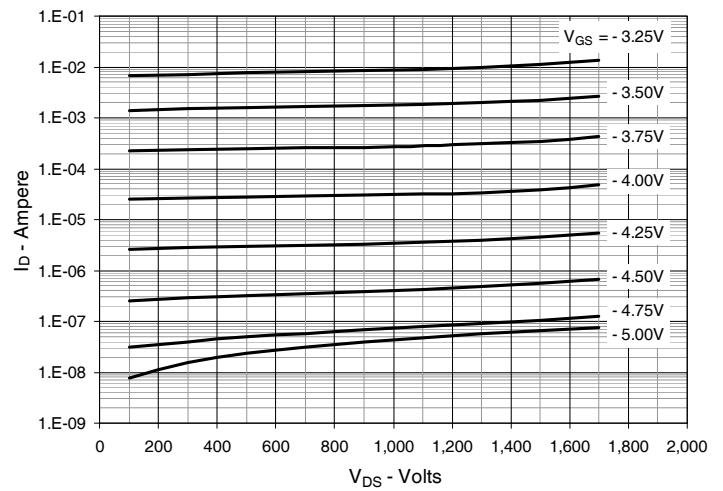


Fig. 5. Drain Current @ $T_J = 100^\circ\text{C}$

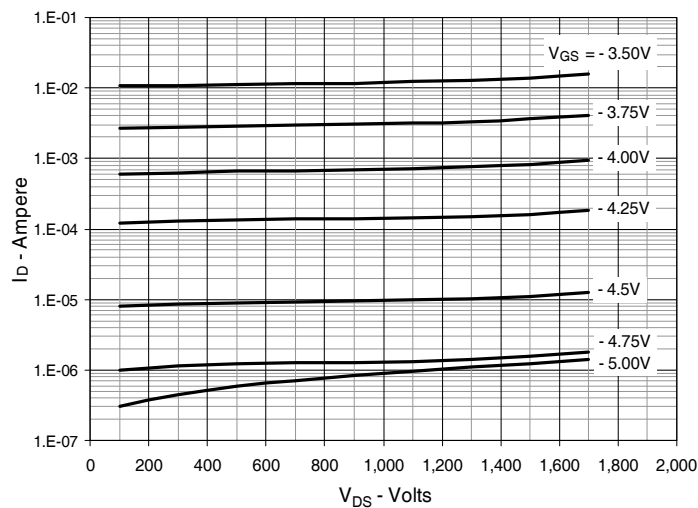


Fig. 6. Dynamic Resistance vs. Gate Voltage

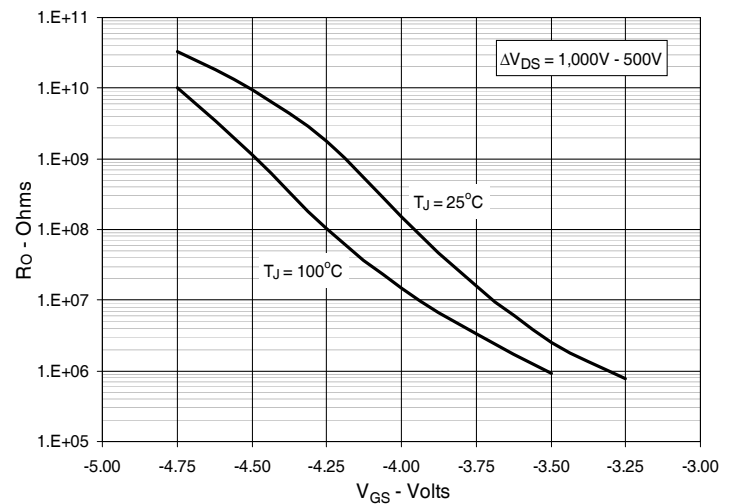


Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

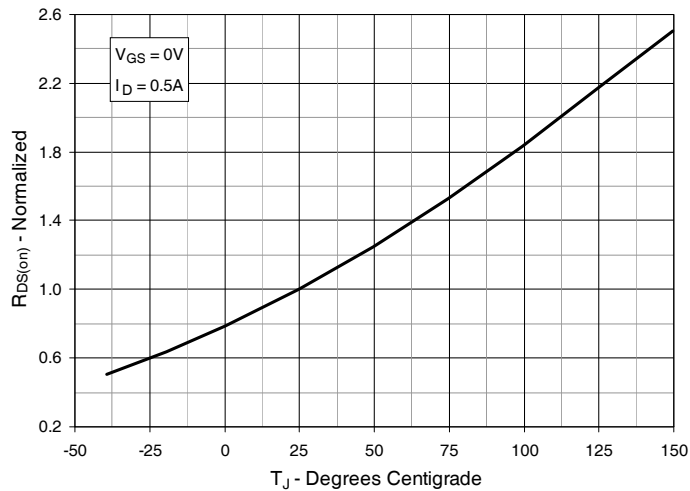


Fig. 8. $R_{DS(on)}$ Normalized to $I_D = 0.5A$ Value vs. Drain Current

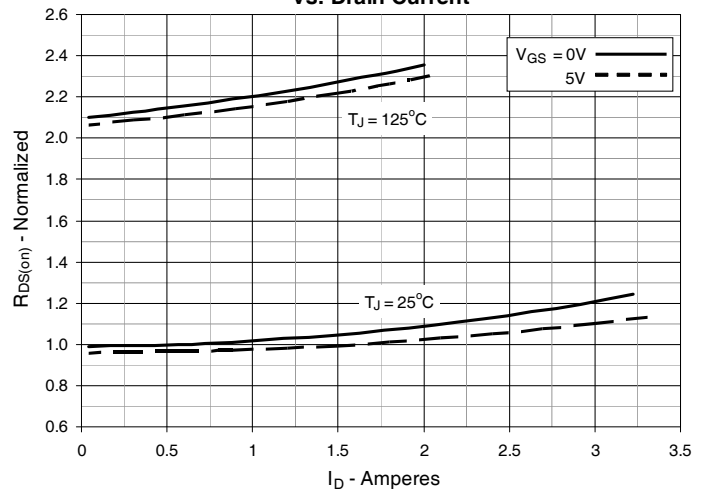


Fig. 9. Input Admittance

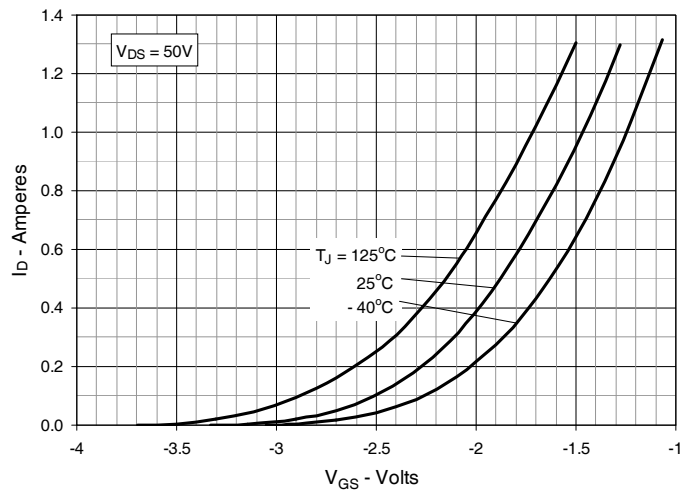


Fig. 10. Transconductance

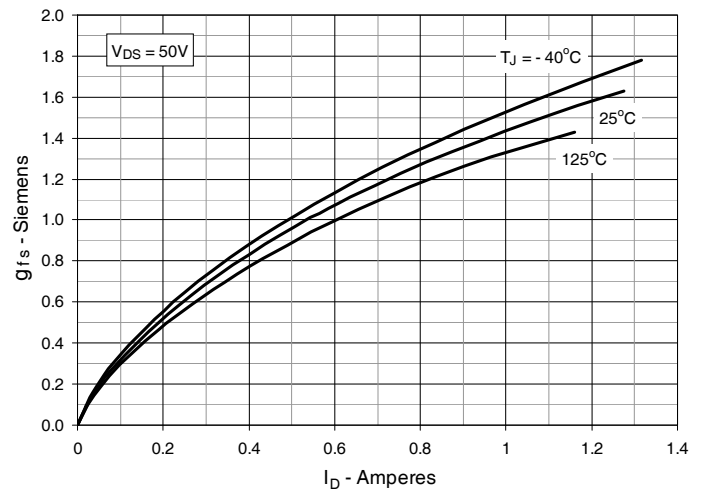


Fig. 11. Normalized Breakdown and Threshold Voltages vs. Junction Temperature

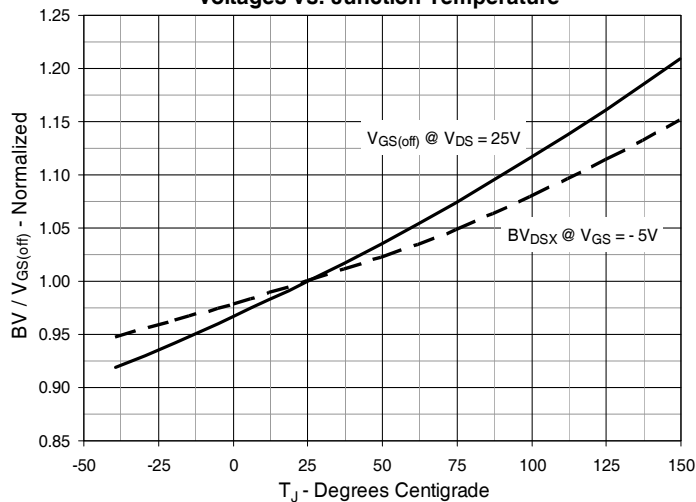


Fig. 12. Forward Voltage Drop of Intrinsic Diode

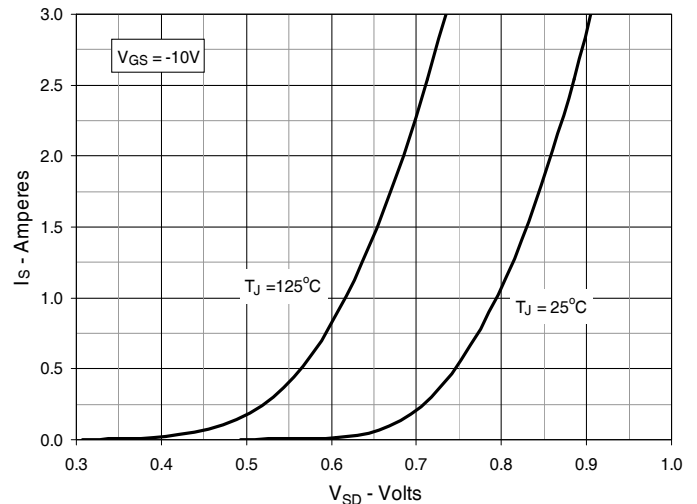


Fig. 13. Capacitance

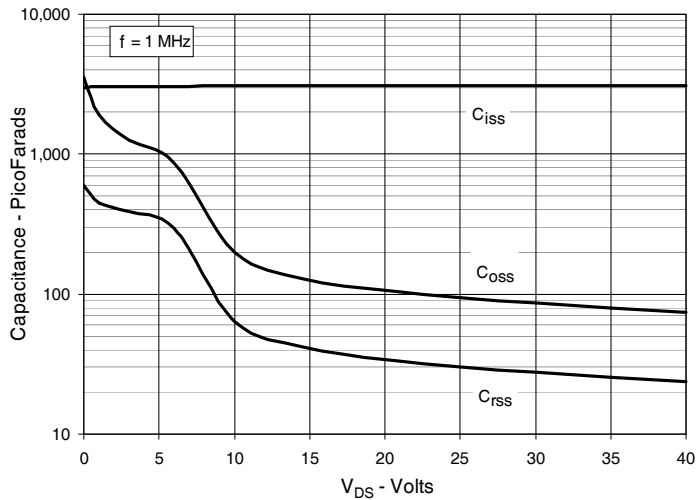


Fig. 14. Gate Charge

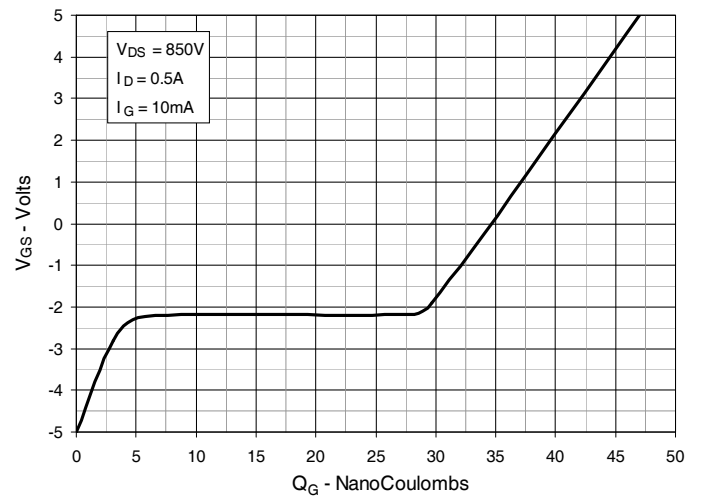


Fig. 15. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$

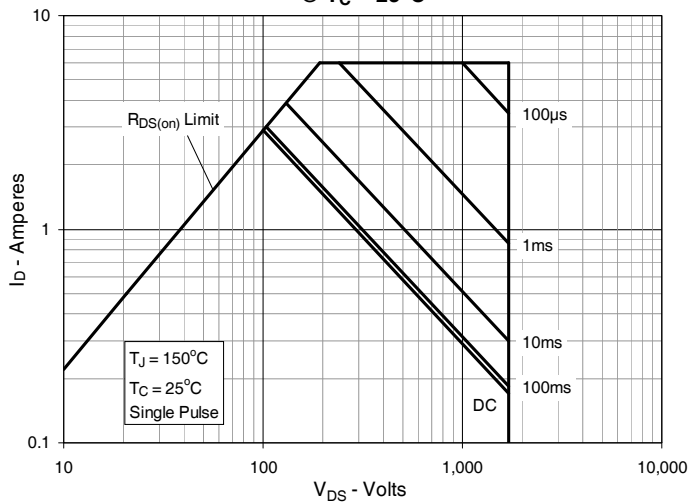


Fig. 16. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$

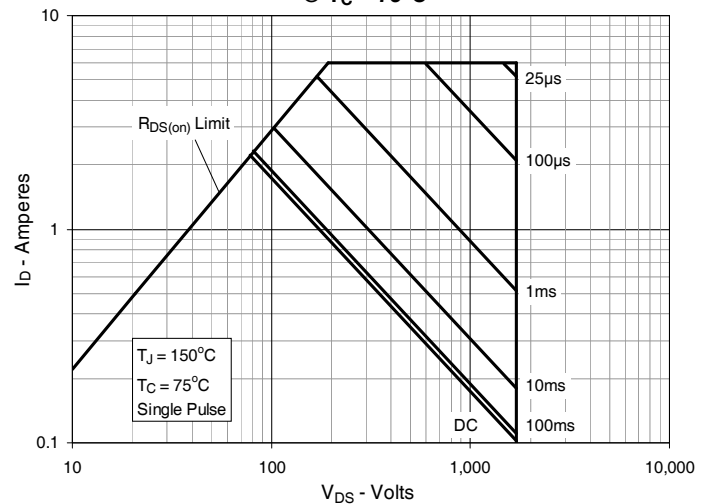
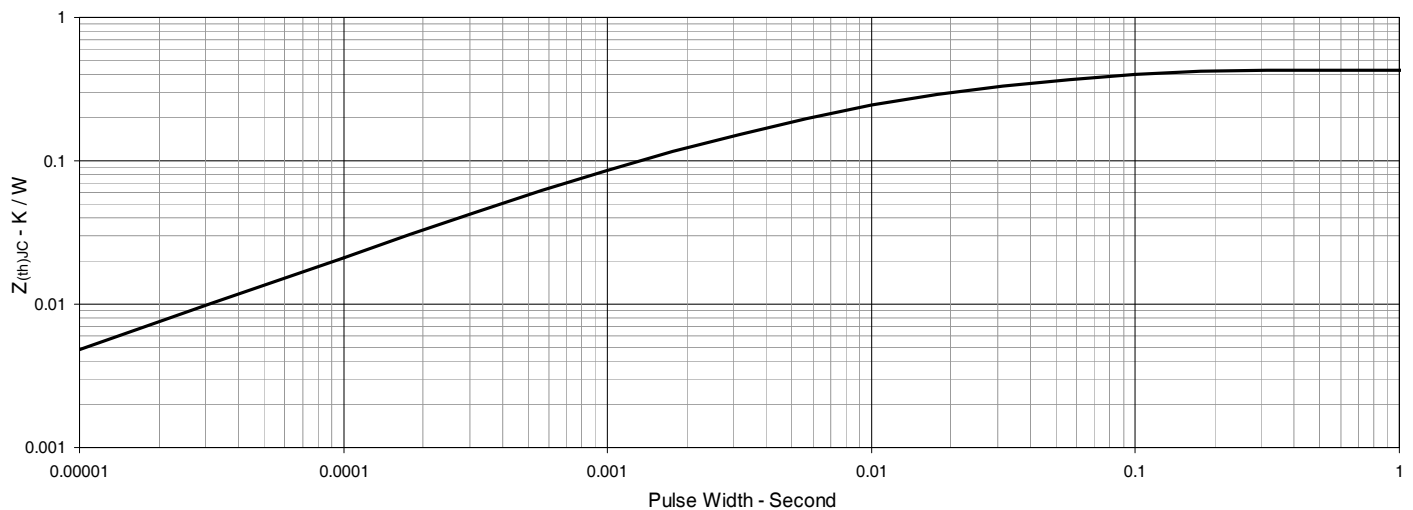


Fig. 17. Maximum Transient Thermal Impedance





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